



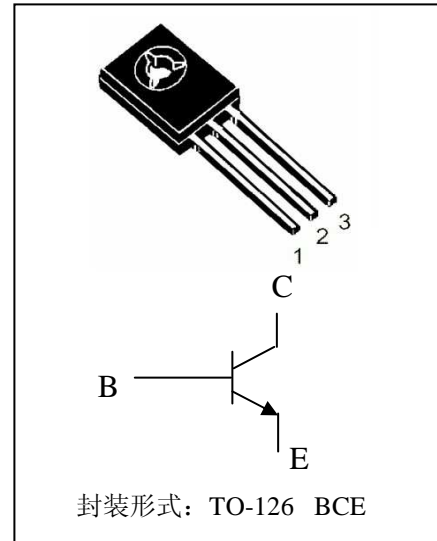
NPN高压开关晶体管/NPN High Voltage Switching Transistor

- 特点: ■击穿的电压稳定 ■开关速度快 ■安全工作区宽 ■符合ROHS规范
- FEATURES: ■HIGH VOLTAGE CAPABILITY ■HIGH SPEED SWITCHING ■WIDE SOA ■ROHS COMPLIANT
- 应用 ■节能灯 ■电子镇流器 ■电子变压器等开关电路
- APPLICATION: ■FLUORESCENT LAMP ■ELECTRONIC BALLAST ■ELECTRONIC TRANSFORMER ECT.

●最大额定值 (TC=25°C)

●Absolute Maximum Ratings (Tc=25°C)

参数名称 PARAMETER	符号 SYMBOL	额定值 VALUE	单位 UNIT
集电极-基极电压 Collector-Base Voltage	VCBO	600	V
集电极-发射极电压 Collector-Emitter Voltage	VCEO	410	V
发射极-基极 Emitter-Base Voltage	VEBO	9	V
集电极电流 Collector Current	Ic	1.0	A
集电极耗散功率 Total Power Dissipation	PC	18	W
最高工作温度 Junction Temperature	Tj	150	°C
贮存温度 Storage Temperature	TsTg	-55-150	°C



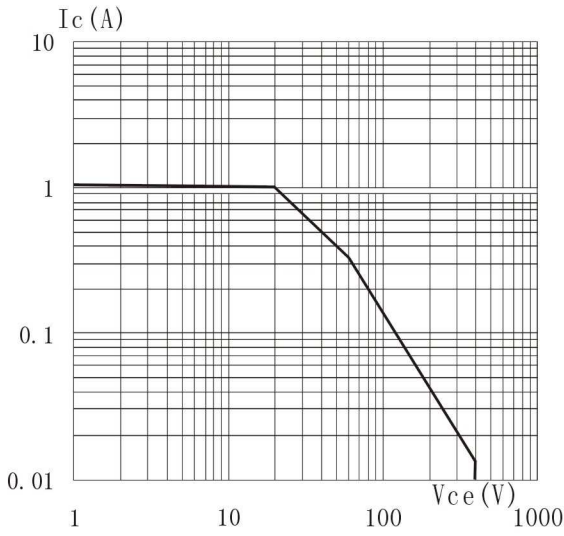
电特性 (TC=25°C)

Electrical Characteristics (Tc=25°C)

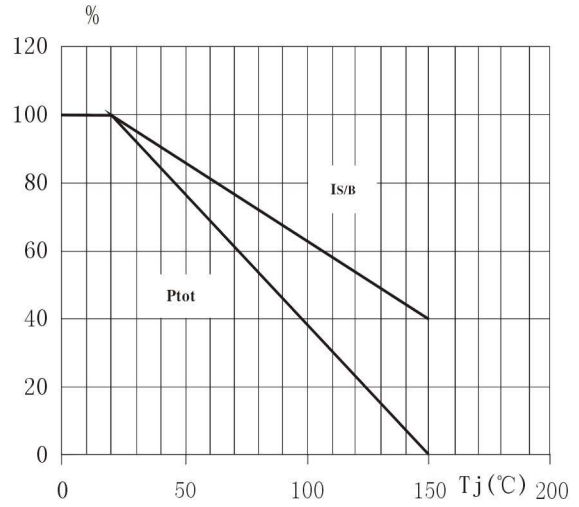
参数名称 CHARACTERISTICS	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	最大值 MAX	单位 UNIT
集电极-基极截止电流 Collector-Base Cutoff Current	ICBO	V _{CB} =600V		5	uA
集电极-发射极截止电流 Collector-Emitter Cutoff Current	ICEO	V _{CE} =410V, I _B =0		10	uA
集电极-发射极电压 Collector-Emitter Voltage	VCEO	I _C =10mA, I _B =0	410		V
发射极-基极电压 Collector-Base Voltage	VEBO	I _E =1mA, I _C =0	9		V
集电极-发射极饱和压降 Collector-Emitter Saturation Voltage	V _{cesat}	I _C =200mA, I _B =40mA		0.3	
		I _C =500mA, I _B =100mA		0.45	V
		I _C =1.0A, I _B =0.25A		0.65	V
发射极-基极饱和压降 Base-Emitter Saturation Voltage	V _{besat}	I _C =1.0A, I _B =0.25A		1.2	V
电流放大倍数 DC Current Gain	H _{fe}	V _{CE} =5V, I _C =200uA	8		
		V _{CE} =5V, I _C =200mA	15	30	
		V _{CE} =5V, I _C =1A	6		
贮存时间 Storage Time	t _s	V _{CC} =5V I _C =0.25A (UI9600)	1.5	2.5	us
下降时间 falling time	t _f			0.8	



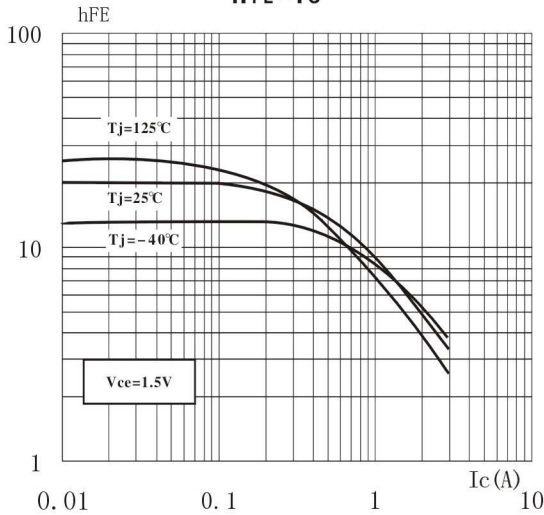
SOA(DC)



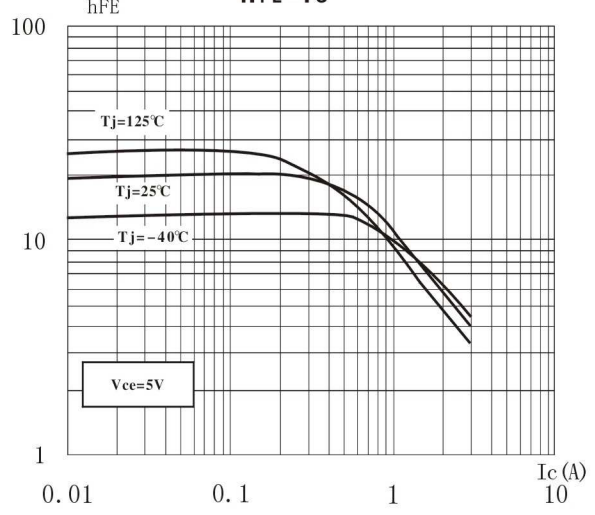
$P_c \propto T_j$



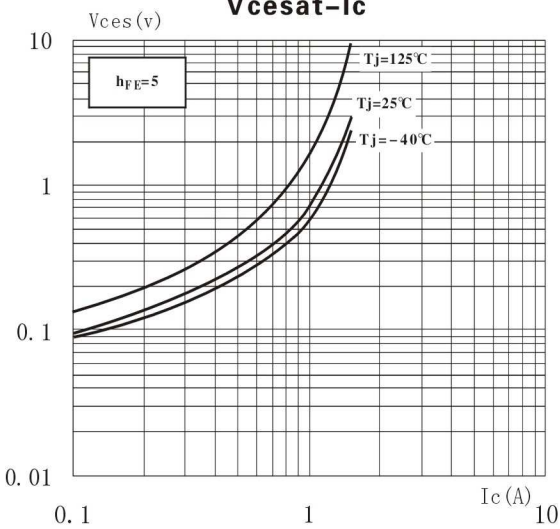
$h_{FE}-I_c$



$h_{FE}-I_c$



$V_{cesat}-I_c$



$V_{besat}-I_c$

